



IRFL014PBF Information



For Reference Only

Part Number IRFL014PBF **Manufacturer** Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 60V 2.7A SOT223

Package TO-261-4, TO-261AA

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









IRFL014PBF Specifications

Manufacturer Part Number IRFL014PBF Manufacturer Vishay Siliconix Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-261-4, TO-261AA Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 2.7A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 11nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 300pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 2W (Ta), 3.1W (Tc) Rds On (Max) @ Id, Vgs 200 mOhm @ 1.6A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-223 Package / Case TO-261-4, TO-261AA		
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FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C2.7A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs11nC @ 10VInput Capacitance (Ciss) (Max) @ Vds300pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)2W (Ta), 3.1W (Tc)Rds On (Max) @ Id, Vgs200 mOhm @ 1.6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-223Package / CaseTO-261-4, TO-261AA	Package	TO-261-4, TO-261AA
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 2.7A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case MOSFET (Metal Oxide) 60V 2.7A (Tc) 2.7A (Tc) 10V 4V @ 250μA 4V @ 250μA 300pF @ 25V 4V @ 250μA 20V Tinc @ 10V 300pF @ 25V 4V @ 25V 4V @ 20V 50V 50V 50V 50V 50V 50V 50V	Series	-
Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C2.7A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs11nC @ 10VInput Capacitance (Ciss) (Max) @ Vds300pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)2W (Ta), 3.1W (Tc)Rds On (Max) @ Id, Vgs200 mOhm @ 1.6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-223Package / CaseTO-261-4, TO-261AA	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C2.7A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs11nC @ 10VInput Capacitance (Ciss) (Max) @ Vds300pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)2W (Ta), 3.1W (Tc)Rds On (Max) @ Id, Vgs200 mOhm @ 1.6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-223Package / CaseTO-261-4, TO-261AA	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Surplier Device Package Package / Case 10V 300pF @ 25V ±20V	Drain to Source Voltage (Vdss)	60V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case 4V @ 250μA 11nC @ 10V 11nC @ 10V 120V FET (Pature	Current - Continuous Drain (Id) @ 25°C	2.7A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 11nC @ 10V 300pF @ 25V 20V ±20V Example (Ta), 3.1W (Tc) 2W (Ta), 3.1W (Tc) 2W (Ta), 3.1W (Tc) Surface Mount 50rport (TJ) Surface Mount Supplier Device Package TO-261-4, TO-261AA	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Coperating Type Surface Mount Supplier Device Package Package / Case 300pF @ 25V 20V 20V 20V Capacitance (Ciss) (Max) @ Vds 2W (Ta), 3.1W (Tc) 200 mOhm @ 1.6A, 10V 200 mOhm @ 1.6A, 10V 7-55°C ~ 150°C (TJ) Surface Mount Supplier Device Package SOT-223 Package / Case	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)2W (Ta), 3.1W (Tc)Rds On (Max) @ Id, Vgs200 mOhm @ 1.6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-223Package / CaseTO-261-4, TO-261AA	Gate Charge (Qg) (Max) @ Vgs	11nC @ 10V
FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 200 mOhm @ 1.6A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case TO-261-4, TO-261AA	Input Capacitance (Ciss) (Max) @ Vds	300pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 200 mOhm @ 1.6A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case TO-261-4, TO-261AA	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs200 mOhm @ 1.6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-223Package / CaseTO-261-4, TO-261AA	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-223 Package / Case TO-261-4, TO-261AA	Power Dissipation (Max)	2W (Ta), 3.1W (Tc)
Mounting Type Surface Mount Supplier Device Package SOT-223 Package / Case TO-261-4, TO-261AA	Rds On (Max) @ Id, Vgs	200 mOhm @ 1.6A, 10V
Supplier Device Package SOT-223 Package / Case TO-261-4, TO-261AA	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-261-4, TO-261AA	Mounting Type	Surface Mount
	Supplier Device Package	SOT-223
Report errors?	Package / Case	TO-261-4, TO-261AA
		Report errors?

IRFL014PBF Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRFL014PBF Payment Methods



















IRFL014PBF Shipping Methods













If you have any question about IRFL014PBF, please do not hesitate to contact us!

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